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Erratum to: Controlling *n*-Type Carrier Density from Er Doping of InGaAs with MBE Growth Temperature

PETER G. BURKE,[1,4] TREVOR E. BUEHL,[1] GILLES PERNOT,[3] HONG LU,[1] ALI SHAKOURI,[3] CHRIS J. PALMSTROM,[1,2] JOHN E. BOWERS,[2] and ARTHUR C. GOSSARD[1,2]

1.—Materials Department, University of California, Santa Barbara, CA 93106, USA. 2.—Department of Electrical and Computer Engineering, University of California, Santa Barbara, CA 93106, USA. 3.—Department of Electrical Engineering, University of California, Santa Barbara, CA 93106, USA. 4.—e-mail: peterburke@umail.ucsb.edu

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Gilles Pernot's name was incorrect in the original article. It is correct as presented in this erratum.

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